

1. Scope :

- 1-1. This specification applies to N channel depletion MOSFET chips,
Device no. PM-0303

2. Structure :

- 2-1. Planar type.
- 2-2. Electrodes.
Source : Aluminum alloy .
Gate : Aluminum alloy .
Drain : Gold alloy.

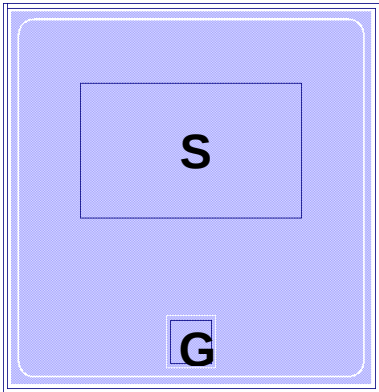
3. Size :

- 3-1. Chip size : 44 mils ×44 mils (1.120 mm ×1.120 mm).
- 3-2. Chip thickness : 12 ±1.5mils (0.305± 0.038mm).
- 3-3. Pad size :
Source : 26.0 mils × 15.4 mils (0.660 mm × 0.390mm).
Gate : 4.9 mils × 5.0 mils (0.124mm × 0.127 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.

4. Absolute maximum rating (Ta = 25 °C)

Parameter	Symbol	Rating	Unit
Continuous drain current VGS=0v	ID(m)	0.3	A
Drain-source Voltage	VDSS	60	V
Gate-source Voltage	VGS	±10	V
Operating junction and storage temperature range	TJ TSTG	-40to+150	°C

Pattern drawing



5. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain to source breakdown voltage	BV _{DSS}	V _{GS} = -5V I _{DS} = 100uA	60			V
Gate to source off voltage	V _{GS(off)}	V _{DS} = 25V I _{DS} = 10uA	-1.8	-2.2	-3.5	V
Gate to source leakage current	I _{GSS}	V _{GS} = ±10V V _{DS} = 0V		± 0.07	± 1	μA
Drain to source leakage current	I _{D(OFF)}	V _{GS} = -5V V _{DS} = 60V			1	μA
Drain to source on resistance	R _{DS(on)}	V _{GS} = 0V I _D = 100mA		0.6	1.0	Ω
Diode forward voltage drop	V _{SD}	V _{GS} = -10V I _{SD} = 100mA		0.84	1.8	V

